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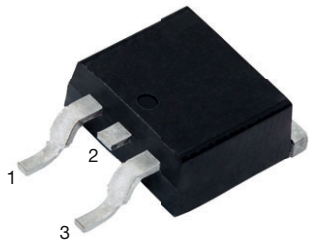
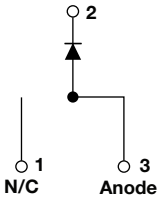
HEXFRED®
Ultrafast Soft Recovery Diode, 6 A



D²PAK (TO-263AB)



FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT

HALOGEN FREE

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA06TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to “snap-off” during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	6 A
V_R	1200 V
V_F at I_F	2.4 V
t_{rr} (typ.)	26 ns
T_J max.	150 °C
Package	D²PAK (TO-263AB)
Circuit configuration	Single

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V_R		1200	V
Maximum continuous forward current	I_F	T_C = 100 °C	6	A
Single pulse forward current	I_{FSM}		80	
Maximum repetitive forward current	I_{FRM}		24	
Maximum power dissipation	P_D	T_C = 25 °C	62.5	W
		T_C = 100 °C	25	
Operating junction and storage temperature range	T_J, T_{Stg}		-55 to +150	°C

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Cathode to anode breakdown voltage	V_{BR}	I_R = 100 µA	1200	-	-	V
Maximum forward voltage	V_{FM}	I_F = 6.0 A	-	2.7	3.0	V
		I_F = 12 A	-	3.5	3.9	
		I_F = 6.0 A, T_J = 125 °C	-	2.4	2.8	
Maximum reverse leakage current	I_{RM}	V_R = V_R rated	-	0.26	5.0	µA
		T_J = 125 °C, V_R = 0.8 x V_R rated	-	110	500	
Junction capacitance	C_T	V_R = 200 V	-	9.0	14	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body	-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Reverse recovery time	t_{rr}	I_F = 1.0 A, dI_F/dt = 200 A/µs, V_R = 30 V		-	26	-	ns
	t_{rr1}	T_J = 25 °C	I_F = 6.0 A dI_F/dt = 200 A/µs V_R = 200 V	-	53	80	
	t_{rr2}	T_J = 125 °C		-	87	130	
Peak recovery current	I_{RRM1}	T_J = 25 °C		-	4.4	8.0	A
	I_{RRM2}	T_J = 125 °C		-	5.0	9.0	
Reverse recovery charge	Q_{rr1}	T_J = 25 °C		-	116	320	nC
	Q_{rr2}	T_J = 125 °C		-	233	585	
Peak rate of recovery current during t_b	$dI_{(rec)M}/dt1$	T_J = 25 °C		-	180	-	A/µs
	$dI_{(rec)M}/dt2$	T_J = 125 °C		-	100	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Lead temperature	T_{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R_{thJC}		-	-	2.0	K/W
Thermal resistance, junction to ambient	R_{thJA}	Typical socket mount	-	-	80	
Thermal resistance, case to heatsink	R_{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Marking device		Case style D^2PAK (TO-263AB)	HFA06TB120S			

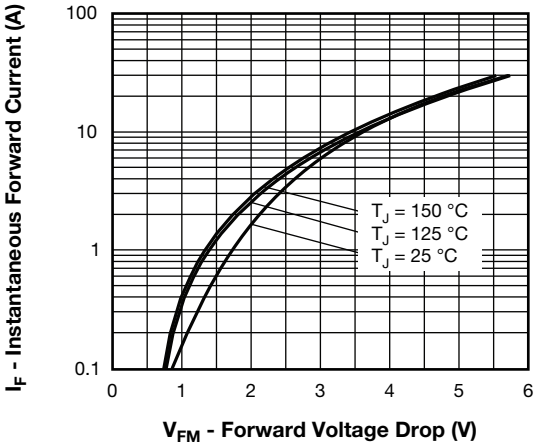


Fig. 1 - Typical Forward Voltage Drop Characteristics

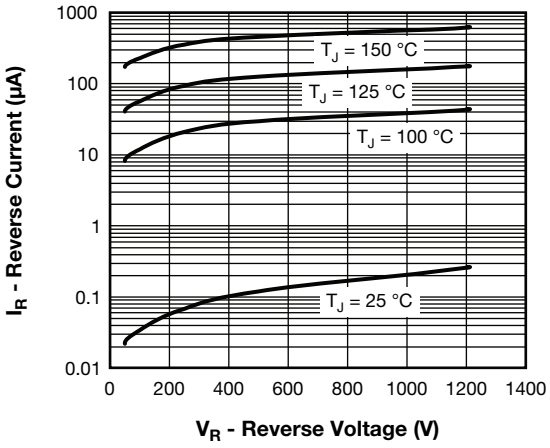


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

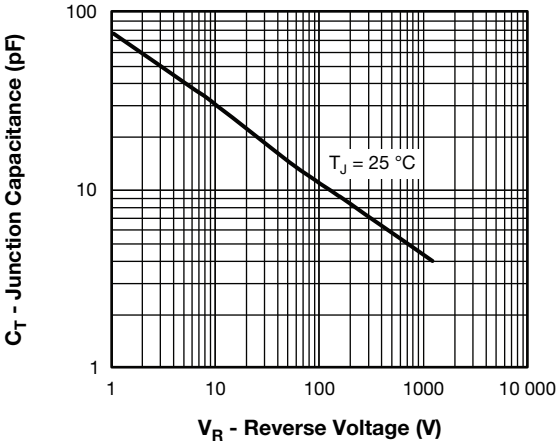


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

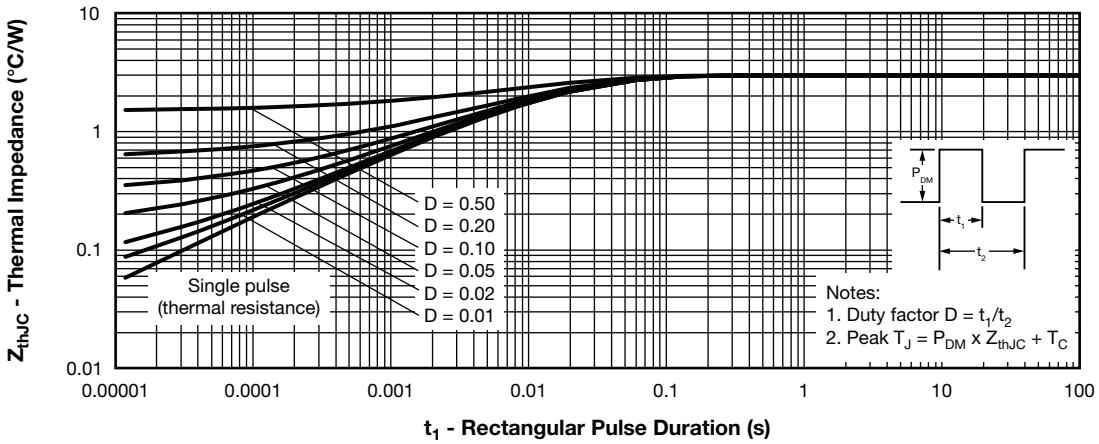


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

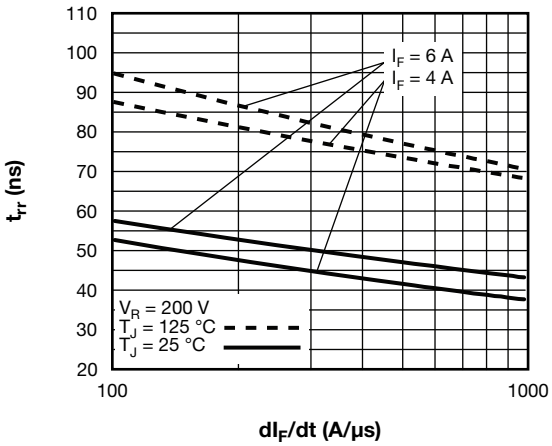


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

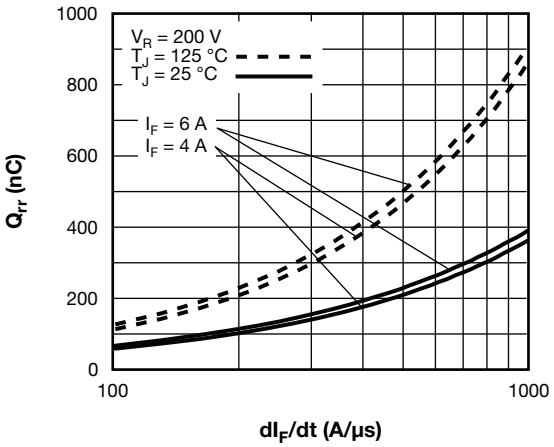


Fig. 7 - Typical Stored Charge vs. dI_F/dt

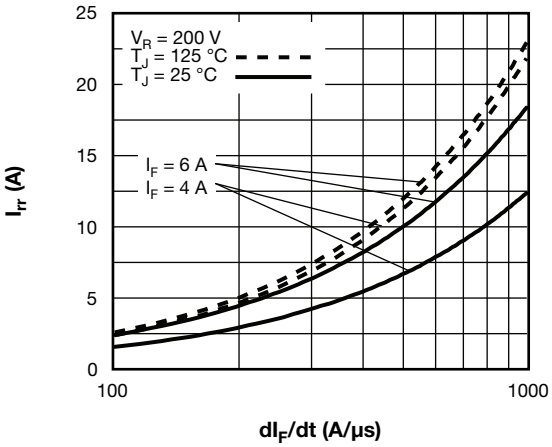


Fig. 6 - Typical Recovery Current vs. dI_F/dt

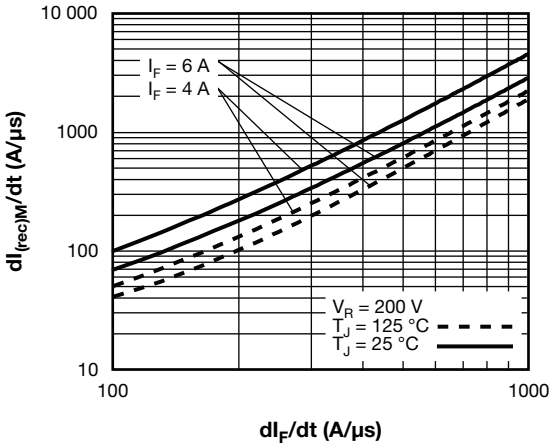
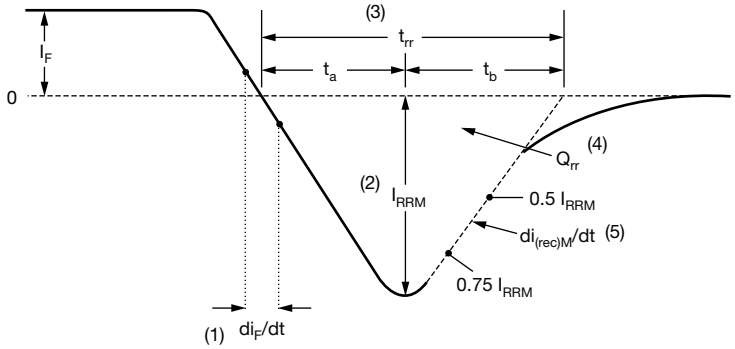


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt



(1) di_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

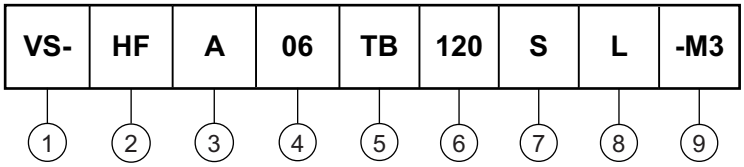
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code

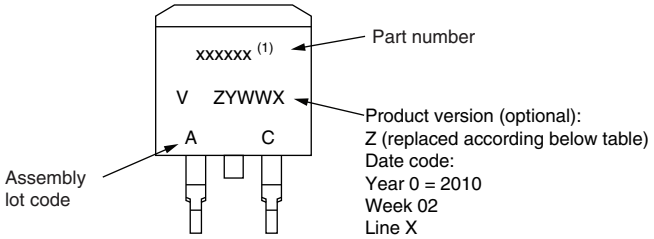


1 - Vishay Semiconductors product
2 - HEXFRED® family
3 - Process designator: A = electron irradiated
4 - Current rating (06 = 6 A)
5 - Package outline (TB = TO-220, 2 leads)
6 - Voltage rating (120 = 1200 V)
7 - S = D^2PAK (TO-263AB)
8 - • None = tube (50 pieces)
• L = tape and reel (left oriented)
• R = tape and reel (right oriented)
9 - Environmental digit:
-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	**QUANTITY PER TUBE**	**MINIMUM ORDER QUANTITY**	**PACKAGING DESCRIPTION**
VS-HFA06TB120S-M3	50	1000	Antistatic plastic tube
VS-HFA06TB120SR-M3	800	800	13" diameter reel
VS-HFA06TB120SL-M3	800	800	13" diameter reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96164
Part marking information	www.vishay.com/doc?95444
Packaging information	www.vishay.com/doc?96424

D^2PAK



Example: This is a xxxxxx (1) with assembly lot code AC, assembled on WW 02, 2010

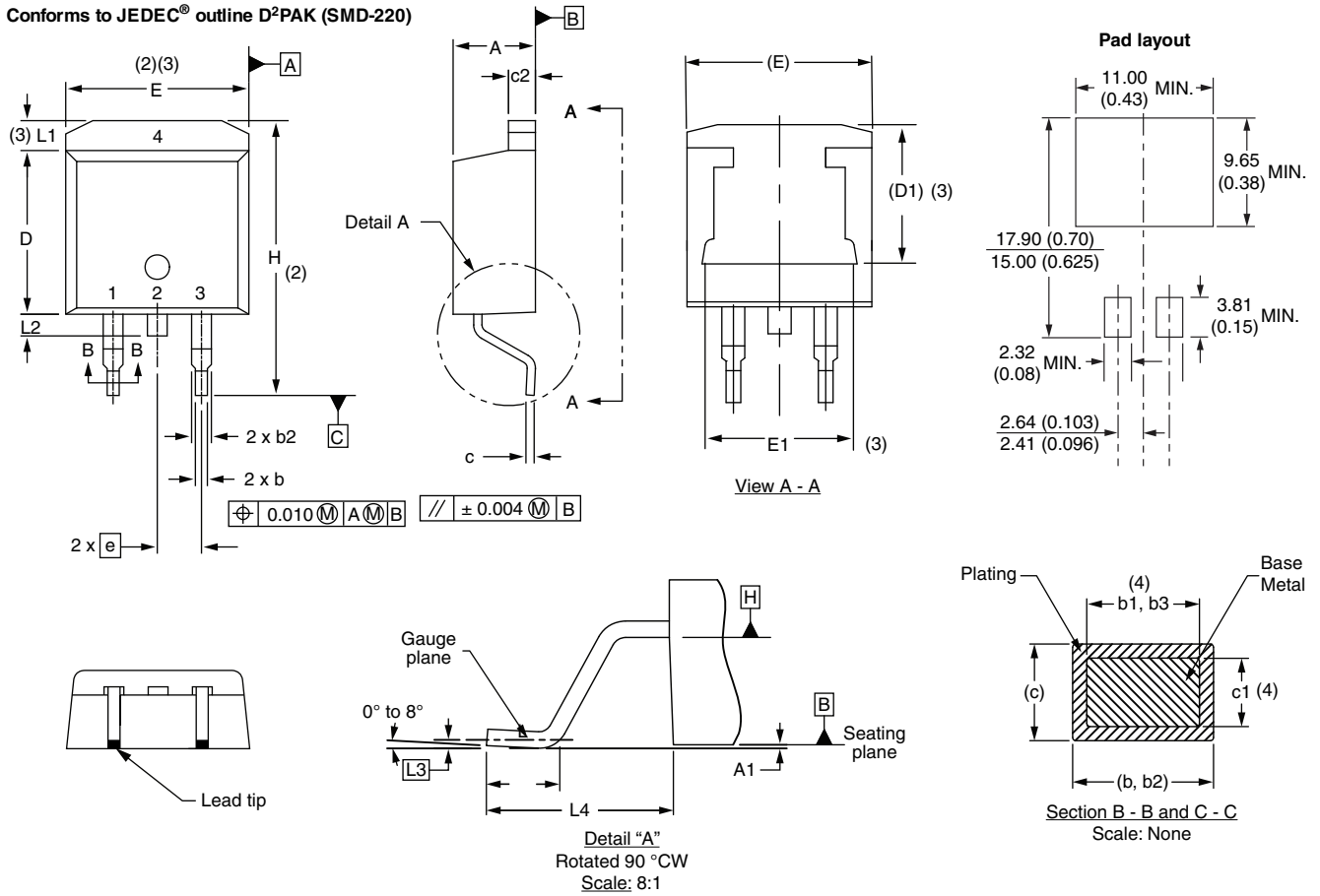
Note

(1) If part number contain “H” as last digit, product is AEC-Q101 qualified

ENVIRONMENTAL NAMING CODE (Z)	PRODUCT DEFINITION
A	Termination lead (Pb)-free
B	Totally lead (Pb)-free
E	RoHS-compliant and termination lead (Pb)-free
F	RoHS-compliant and totally lead (Pb)-free
M	Halogen-free, RoHS-compliant, and termination lead (Pb)-free
N	Halogen-free, RoHS-compliant, and totally lead (Pb)-free
G	Green

D^2PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
c	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

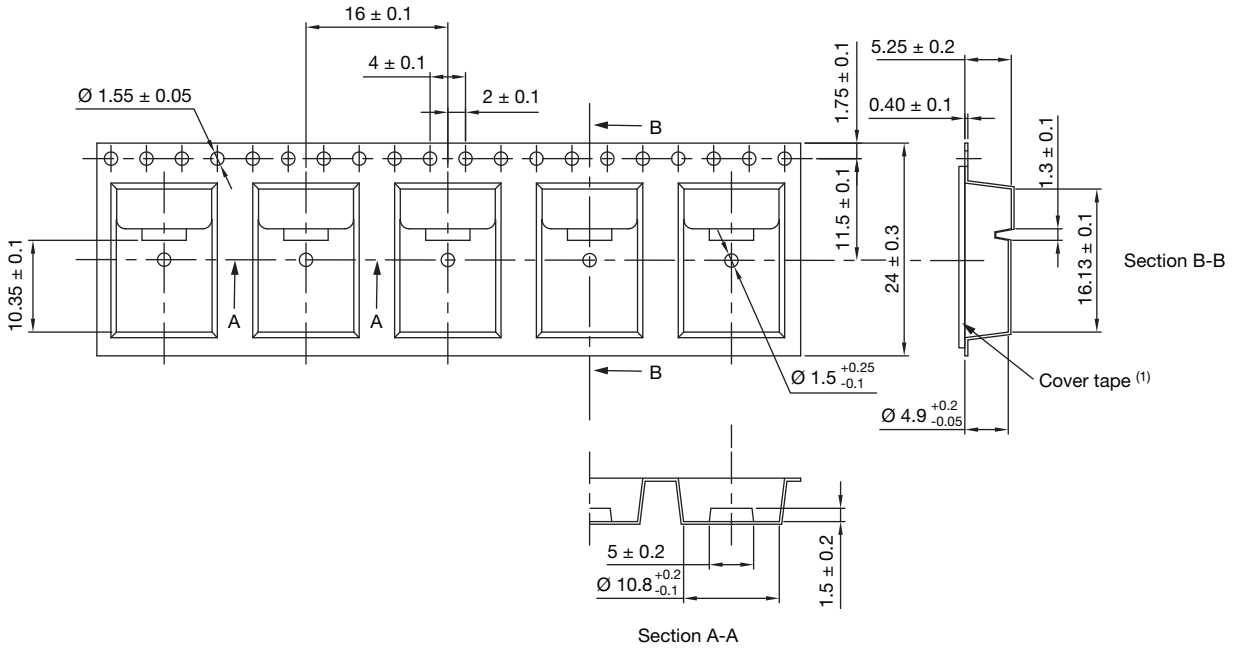
SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
e	2.54 BSC		0.100 BSC		
H	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010 BSC		
L4	4.78	5.28	0.188	0.208	

Notes

(1) Dimensioning and tolerancing per ASME Y14.5 M-1994
(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
(3) Thermal pad contour optional within dimension E, L1, D1 and E1
(4) Dimension b1 and c1 apply to base metal only
(5) Datum A and B to be determined at datum plane H
(6) Controlling dimension: inches
(7) Outline conforms to JEDEC® outline TO-263AB

D²PAK (TO-263AB)

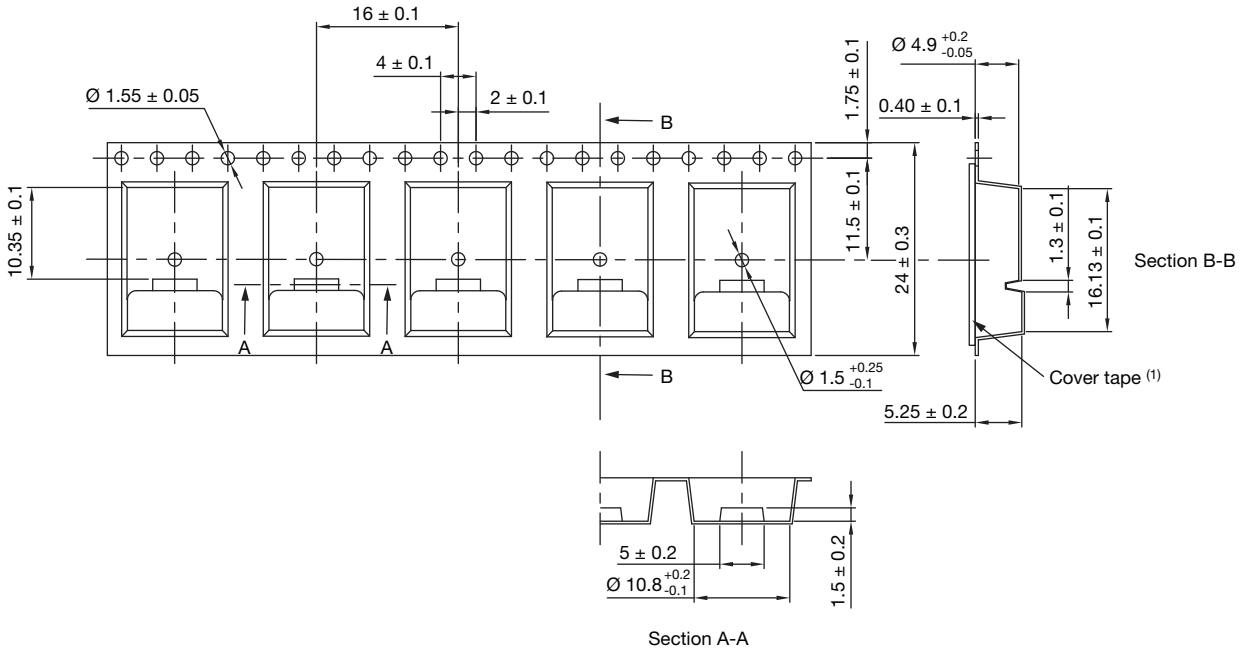
CARRIER TAPE FOR TAPE AND REEL LEFT in millimeters



Note

(1) For dimensions, see next pages

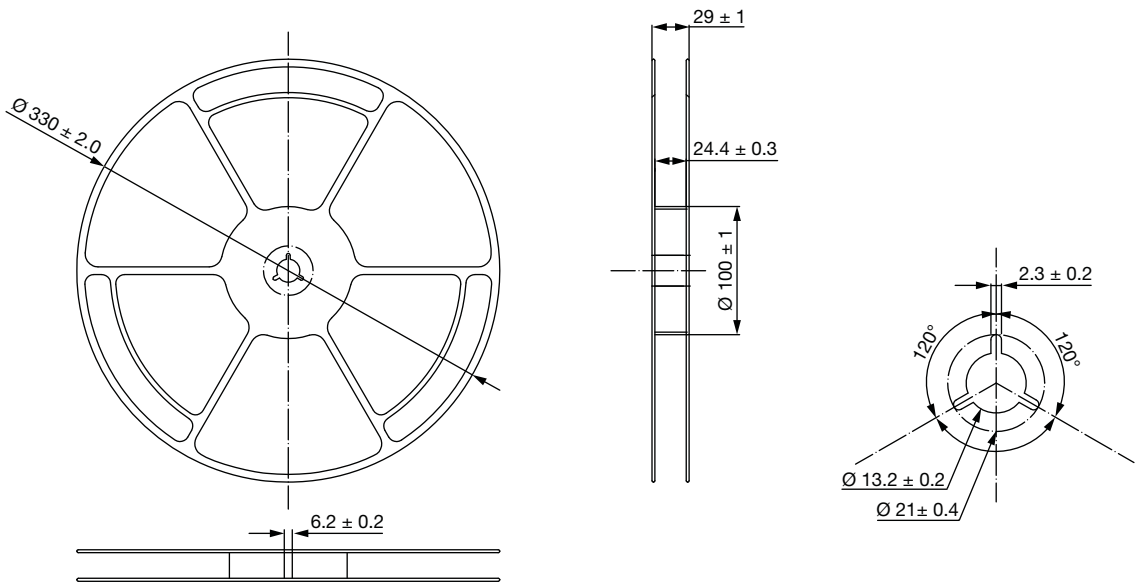
CARRIER TAPE FOR TAPE AND REEL RIGHT in millimeters



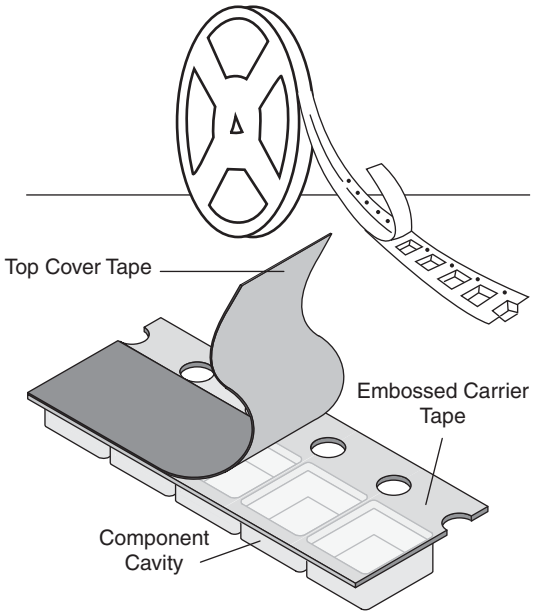
Note

(1) For dimensions, see next pages

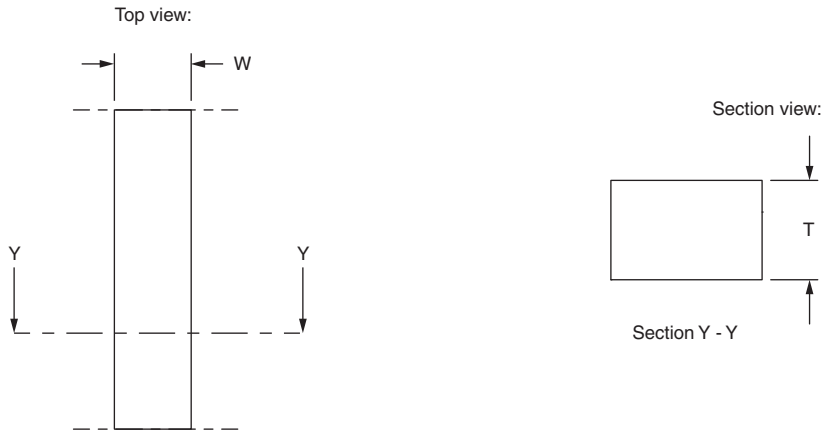
REEL FOR CARRIER TAPE in millimeters



CARRIER TAPE AND REEL PACKAGING D^2PAK (TO-263AB)



COVER TAPE FOR CARRIER TAPE in millimeters



APPLICATION	COVER TAPE WIDTH W	COVER TAPE THICKNESS T	CARRIER TAPE WIDTH	MATERIAL
D^2PAK (TO-263AB)	21.3 ± 0.1	0.060 ± 0.01	24	Antistatic/treated/transparent/polyester

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